

BYV26DGP & BYV26EGP

Vishay General Semiconductor

RoHS

COMPLIANT

Glass Passivated Ultrafast Rectifier



* Glass Encapsulation technique is covered by Patent No. 3,996,602, brazed-lead assembly to Patent No. 3,930,306

DO-204AC (DO-15)

PRIMARY CHARACTERISTICS					
I _{F(AV)}	1.0 A				
V_{RRM}	800 V, 1000 V				
I _{FSM}	30 A				
t _{rr}	75 ns				
V_{F}	1.3 V				
T _J max.	175 °C				

FEATURES

- Cavity-free glass-passivated junction
- Ultrafast reverse recovery time
- Low forward voltage drop
- · Low switching losses, high efficiency
- zew emierning recese, ringir emerer.
- High forward surge capability
- Meets environmental standard MIL-S-19500
- Solder dip 260 °C, 40 s
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

TYPICAL APPLICATIONS

For use in high frequency rectification and freewheeling application in switching mode converters and inverters for consumer, computer and telecommunication.

MECHANICAL DATA

Case: DO-204AC, molded epoxy over glass body

Epoxy meets UL 94V-0 flammability rating

Terminals: Matte tin plated leads, solderable per

J-STD-002 and JESD22-B102

E3 suffix for consumer grade, meets JESD 201 class 1A whisker test, HE3 suffix for high reliability grade (AEC Q101 qualified), meets JESD 201 class 2 whisker test

Polarity: Color band denotes cathode end

MAXIMUM RATINGS (T _A = 25 °C unless otherwise noted)					
PARAMETER	SYMBOL	BYV26DGP	BYV26EGP	UNIT	
Maximum repetitive peak reverse voltage	V _{RRM}	800	1000	V	
Maximum RMS voltage	V _{RMS}	560	700	V	
Maximum DC blocking voltage	V _{DC}	800	1000	V	
Maximum average forward rectified current 0.375" (9.5 mm) lead length (Fig. 1)	I _{F(AV)}	1.0		А	
Peak forward surge current 10 ms single half sine-wave superimposed on rated load	I _{FSM}	30		А	
Non repetitive peak reverse energy (1)	E _{RSM}	10		mj	
Operating junction and storage temperature range	T _J , T _{STG}	- 65 to + 175			

Note:

Peak reverse energy measured at $I_R = 400$ mA, $T_J = T_J$ max. on inductive load, $t = 20 \mu s$

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ELECTRICAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)						
PARAMETER	TEST CONDITIONS		SYMBOL	BYV26DGP	BYV26EGP	UNIT
Minimum avalanche breakdown voltage	100 μΑ		V _{BR}	900 1100		V
Maximum instantaneous forward voltage	1.0 A	T _J = 25 °C T _J = 175 °C	V _F	2.5 1.3		V
Maximum DC reverse current at rated DC blocking voltage		T _A = 25 °C T _A = 165 °C	I _R	5.0 150		μΑ
Max. reverse recovery time	I _F = 0.5 A, I _R = 1.0 A, I _{rr} = 0.25 A		t _{rr}	75		ns
Typical junction capacitance	4.0 V, 1 N	1Hz	CJ	15		pF

THERMAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)					
PARAMETER	SYMBOL	BYV26DGP BYV26EGP		UNIT	
Typical thermal resistance (1)(2)	$R_{ hetaJA} \ R_{ hetaJL}$	70 16		°C/W	

Notes:

- (1) Thermal resistance from junction to ambient at 0.375" (9.5 mm) lead length, mounted on P.C.B. with 0.5 x 0.5" (12 x 12 mm) copper pads
- (2) Thermal resistance from junction to lead at 0.375" (9.5 mm) lead length with both leads attached to heatsink

ORDERING INFORMATION (Example)						
PREFERRED P/N	UNIT WEIGHT (g)	PREFERRED PACKAGE CODE	BASE QUANTITY	DELIVERY MODE		
BYV26EGP-E3/54	0.428	54	4000	13" diameter paper tape and reel		
BYV26EGP-E3/73	0.428	73	2000	Ammo pack packaging		
BYV26EGPHE3/54 (1)	0.428	54	4000	13" diameter paper tape and reel		
BYV26EGPHE3/73 (1)	0.428	73	2000	Ammo pack packaging		

Note:

RATINGS AND CHARACTERISTICS CURVES

(T_A = 25 °C unless otherwise noted)

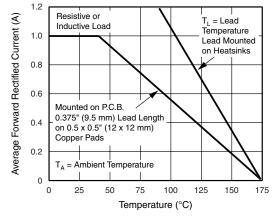


Figure 1. Maximum Forward Current Derating Curve

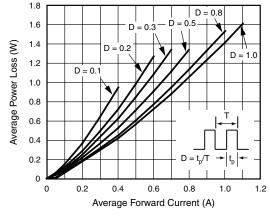


Figure 2. Forward Power Loss Characteristics

⁽¹⁾ Automotive grade AEC Q101 qualified



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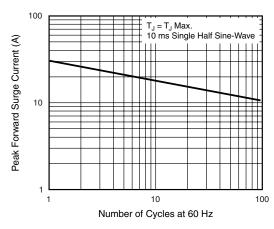


Figure 3. Maximum Non-Repetitive Peak Forward Surge Current

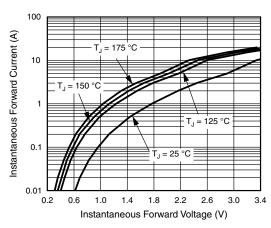


Figure 4. Typical Instantaneous Forward Voltage Characteristics

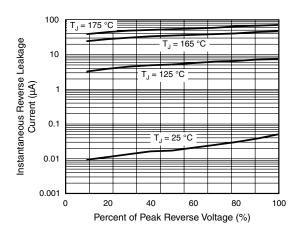


Figure 5. Typical Reverse Leakage Characteristics

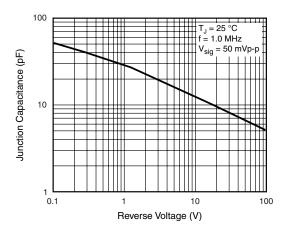


Figure 6. Typical Junction Capacitance

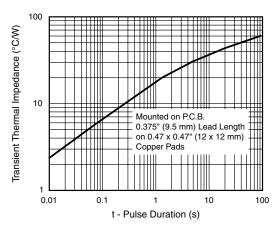


Figure 7. Typical Transient Thermal Impedance

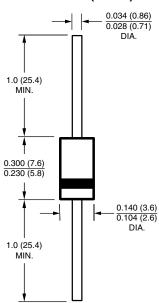
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PACKAGE OUTLINE DIMENSIONS in inches (millimeters)

DO-204AC (DO-15)





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